

00862.022541



PATENT APPLICATION

2812
#3/IPS
D. Nguyen
6/25/02

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

In re Application of:

MASATAKA ITO

Application No.: 10/091,461

Filed: March 7, 2002

For: SOI SUBSTRATE, ANNEALING
METHOD THEREFOR,
SEMICONDUCTOR DEVICE
HAVING THE SOI SUBSTRATE,
AND METHOD OF
MANUFACTURING THE SAME

Examiner: Not Yet Assigned

Group Art Unit: 2812

May 14, 2002

TECHNOLOGY CENTER 2800

MAY 16 2002

RECEIVED

Commissioner for Patents
Washington, D.C. 20231

INFORMATION DISCLOSURE STATEMENT

Sir:

In compliance with the duty of disclosure under 37 C.F.R. § 1.56 and in accordance with the practice under 37 C.F.R. §§ 1.97 and 1.98, the Examiner's attention is directed to the documents listed below and on attached Form PTO-1449. Copies of the listed documents are also enclosed.

U.S. Patent No. 5,869,387

U.S. Patent No. 6,171,982

Japan 05-152230

Japan 05-217821

Japan 11-265893

"Nano-Defects In Commercial Bonded SOI And SIMOX", D.K.
Sadana et al., 1994 IEEE International SOI Conference Proceedings,
October 1994, pp. 111-112.

"Extremely Low Si Etching (<1nm) During Hydrogen Annealing of Silicon-on-Insulator", N. Sato et al., Extended Abstracts of the 1998 International Conference on Solid State Devices And Materials, Hiroshima, 1998, pp.298-299.

"Suppression of Si Etching During Hydrogen Annealing of Silicon-on-Insulator" N. Sato et al., 1998 IEEE International SOI Conference Proceedings, October 1998, pp. 17-18.

"Hydrogen Annealing Treatment Used To Obtain High Quality SOI Surfaces" H. Moriceau et al., 1998 IEEE International SOI Conference Proceedings, October 1998, pp. 37-38.

"Defect Reduction of Bonded SOI Wafers By Post Anneal Process In H₂ Ambient", N. Tate et al., 1998 IEEE International SOI Conference Proceedings, October 1998, pp. 141-142

English-language abstracts for the above-listed Japanese patent documents are enclosed. Further, U.S. Patent No. 5,869,387 is believed to be an English language counterpart to JP 5-217821.

Inasmuch as the subject application has not yet received a first Office Action, it is believed that this Information Disclosure Statement is timely. See 37 C.F.R. § 1.97(b)(3).

Accordingly, the Examiner is urged to study this information in its entirety and to form an independent determination of the materiality of the information to the claimed invention. Additionally, the Examiner is requested to indicate that this information has been considered by initialing the appropriate portion of Form PTO-1449.

Applicant's undersigned attorney may be reached in our Costa Mesa, California office by telephone at (714) 540-8700. All correspondence should continue to be directed to our address given below.

Respectfully submitted,


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FORM PTO 1449 (modified)

U.S. DEPARTMENT OF COMMERCE
PATENT AND TRADEMARK OFFICE

LIST OF REFERENCES CITED BY APPLICANT(S)
(Use several sheets if necessary)

MAY 15 2002

ATTY DOCKET NO. 00862.022541

APPLICATION NO. 10/091,461

APPLICANT **MASATAKA ITO**

FILING DATE **March 7, 2002**

GROUP **2812**

U.S. PATENT DOCUMENTS						
*EXAMINER INITIAL	DOCUMENT NUMBER	DATE	NAME	CLASS	SUBCLASS	FILING DATE IF APPROPRIATE
	5,869,387	02/09/1999	Sato et al.	438	459	03/13/1995
	6,171,982	01/09/2001	Sato	438	795	12/22/1998

FOREIGN PATENT DOCUMENTS						
	DOCUMENT NUMBER	DATE	COUNTRY	CLASS	SUBCLASS	TRANSLATION YES/NO/ OR ABSTRACT
	05-152230	06/18/1993	Japan			Abstract
	05-217821	08/27/1993	Japan			Abstract
	11-265893	09/28/1999	Japan			Abstract

OTHER DOCUMENT(S) (Including Author, Title, Date, Pertinent Pages, Etc.)

	"Nano-Defects In Commercial Bonded SOI And SIMOX", D.K. Sadana et al., 1994 IEEE International SOI Conference Proceedings, October 1994, pp. 111-112.
	"Extremely Low Si Etching (<1nm) During Hydrogen Annealing of Silicon-on-Insulator", N. Sato et al., Extended Abstracts of the 1998 International Conference on Solid State Devices And Materials, Hiroshima, 1998, pp.298-299.
	"Suppression of Si Etching During Hydrogen Annealing of Silicon-on-Insulator" N. Sato et al., 1998 IEEE International SOI Conference Proceedings, October 1998, pp. 17-18.
	"Hydrogen Annealing Treatment Used To Obtain High Quality SOI Surfaces" H. Moriceau et al., 1998 IEEE International SOI Conference Proceedings, October 1998, pp. 37-38.
	"Defect Reduction Of Bonded SOI Wafers By Post Anneal Process In H ₂ Ambient", N. Tate et al., 1998 IEEE International SOI Conference Proceedings, October 1998, pp. 141-142

EXAMINER	DATE CONSIDERED
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*EXAMINER: Initial if reference considered, whether or not citation is in conformance with MPEP 609; Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.

Sheet 1 of 1